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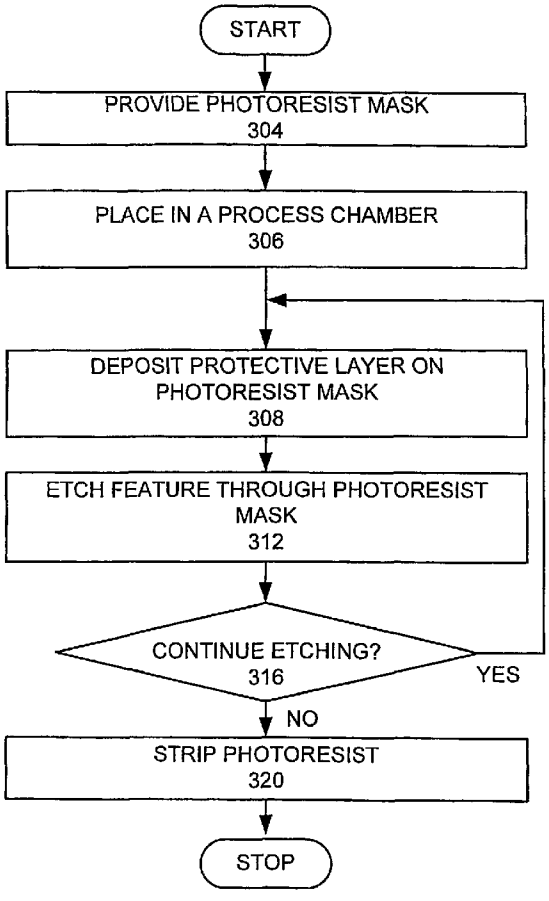
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(54) Title: A METHOD FOR PLASMA ETCHING PERFORMANCE ENHANCEMENT



(57) Abstract: A method for etching a feature in a layer through an etching mask is provided. A protective layer is formed on exposed surfaces of the etching mask and vertical sidewalls of the feature with a passivation gas mixture. The feature is etched through the etching mask with reactive etching mixtures containing at least one etching chemical and at least one passivation chemical.

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